



Ruttonsha International Rectifier Ltd.

SILICON CONTROL RECTIFIER

High Power Thyristor
Hockey Puk Version
QQ-PUK Series 7000PQQ
Type:- 7000PQQ 60

FEATURES

- # Center amplifying gate.
- # Metal case with ceramic insulator.
- # High profile hockey - puk.

TYPICAL APPLICATION

- # DC Motor control (e.g. for machine tools).
- # Controlled rectifiers (e.g. for battery charging
Uninterrupted power supply).
- # AC Controllers (e.g. for temperature control lights control).

MAJOR RATING & CHARACTERISTICS

Parameters	7000 PQQ	Units
$I_{T(AV)}$ @ 55°C	6974	A
$I_{T(RMS)}$ @ 25°C	13608	A
I_{TSM} @ 60Hz	65	kA
I^2t @ 60Hz	21.13×10^6	A ² S
$V_{DRM} - V_{RRM}$	200 to 600	V
T_J	-40 to 140	°C

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ELECTRICAL SPECIFICATION

VOLTAGE RATINGS

Type Number	Voltage Code	V_{RMM}/V_{DRM} max. repetitive peak reverse voltage V	V_{RSM} max.Non-repetitive peak reverse voltage V	I_{DRM} / I_{RRM} max. @ 125°C Max. mA
7000 PQQ	20	200	300	100
	40	400	500	
	60	600	700	

ON-STATE CONDUCTION

	Parameter	7000PQQ	Unit	Conditions	
$I_{T(AV)}$	Max, average on-state current @ Case temperature	6974	A	180° conduction, half sine wave	
		55	°C		
$I_{T(RMS)}$	Max, RMS on-state current @25°C	13608	A	as AC switch	
I_{TSM}	Max, peak, one cycle on-state, non-repetitive surge current	65	kA	t = 10ms	Sinusoidall half wave, Initial Tj = Tj max.
I^2t	Maximum I^2t for fusing	21.13×10^6	A ² s	t = 10ms	Sinusoidall half wave, Initial Tj = Tj max.
$V_{T(TO)}$	Threshould voltage	0.853	V	Tj = Tj max.	
r_t	On-state slope resistance	0.029	mΩ	Tj = Tj max,	
V_{TM}	Max, on-state voltage drop	0.95	V	$I_r = 3000$ Amps, 125°C	
I_H	Holding current	1000	mA	Anod supply = 12V, initial $I_r = 30\mu s$, Tj = 25°C	
I_L	Latching current	1	A	Anod supply = 12V, resistive load =1Ω, gate pulse : 10V, 100μs, Tj = 25°C	

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BLOCKING

	Parameter	7000 PQQ	Unit	Conditions
dv/dt	Maximum critical rate of rise off-state voltage	1000	V/ μ s	T _j = 125°C, exponential to 67% rated V _{DRM}
I _{RRM} I _{ORM}	Max. peak reverse and off-state leakage current	100	mA	T _j = 125°C, rated V _{DRM} /V _{RRM} applied
di/dt	Repetitive Critical rate of rise of on-state current	200	A/ μ s	I _{trm} - 2000A, T _j = 125°C

TRIGGERING

	Parameter	7000 PQQ	Unit	Conditions
P _{GM}	Max, peak gate power	30	W	T _j = 125°C, t _p = 100 μ s
P _{G(AV)}	Maximum average gate power	4		T _j = 125°C, f = 50Hz, d% = 50
I _{GM}	Max, peak positive gate current	3.0	A	T _j = 125° C, t _p $\leq$ 5ms
+V _{GM}	Max. peak positive gate voltage	20.0	V	T _j = 125°C t _p $\leq$ 5ms
-V _{GM}	Max. peak negative gate voltage	5.0		
I _{GT}	DC gate current required to trigger	300	mA	VD = 12V.
V _{GT}	DC gate voltage for to trigger	3.0	V	VD = 12V.
I _{GD}	DC gate current not to trigger	10	mA	T _j = T _j max.
V _{GD}	DC gate voltage not to trigger	0.25	V	

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	7000 PQQ	Unit	Conditions
T _J	Max, operating temperature range	-40 to 140	°C	
T _{stg}	Max, storage temperature range	-40 to 150		
R _{thJ-h}	Max, thermal resistance, junction to heat sink	0.011	K/W	Double side cooled.
F	Mounting force $\pm$ 10%	36 to 44	kN	
W t	Approximate Weight	550	g	
	Case style	QQ-PUK		

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OUTLINE DIAGRAM

Q-PUK

